

1-Line Bi-directional TVS Diode

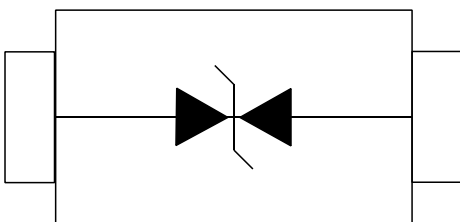
Description

The PESDU4581D3H is a bi-directional high power TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU4581D3H complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small lead -free SOD-323 package. The small size and high ESD surge protection make PESDU4581D3H an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Small SOD-323 package
- Protects one data or power line
- Operating Voltage: 4.5V
- High peak pulse current capability
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 160A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Circuit Diagram

Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Mobile Phones and Accessories
- Battery Protection
- Power Supply Protection
- Hand Held Portable Applications
- Peripherals

Marking Information



48D = Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
PESDU4581D3H	3000/Tape & Reel	7 inch

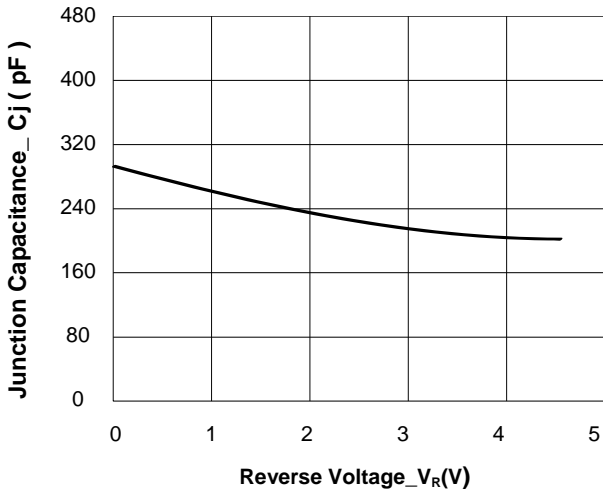
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{PK}	2700	W
Peak Pulse Current (8/20 μs)	I_{PP}	160	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	kV
Operating Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

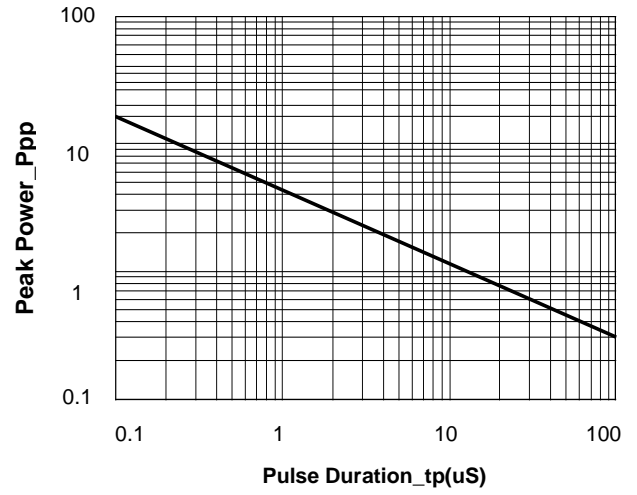
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			4.5	V	
Breakdown Voltage	V_{BR}	4.7			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			1.0	μA	$V_{RWM} = 4.5\text{V}$
Clamping Voltage	V_C			7.5	V	$I_{PP} = 20\text{A}$ (8 x 20 μs pulse)
Clamping Voltage	V_C			17	V	$I_{PP} = 160\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J			300	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

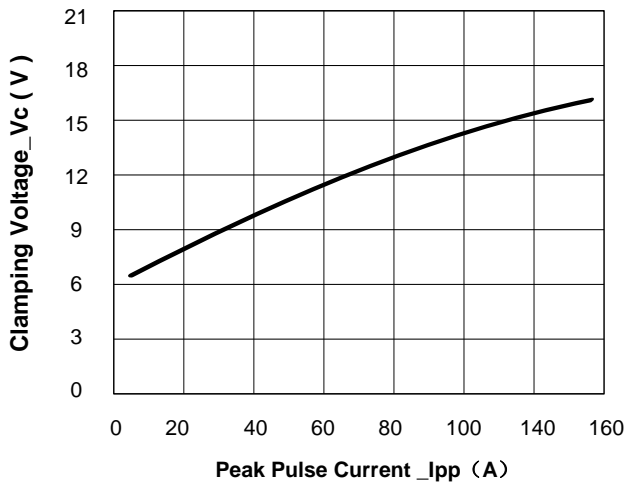
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



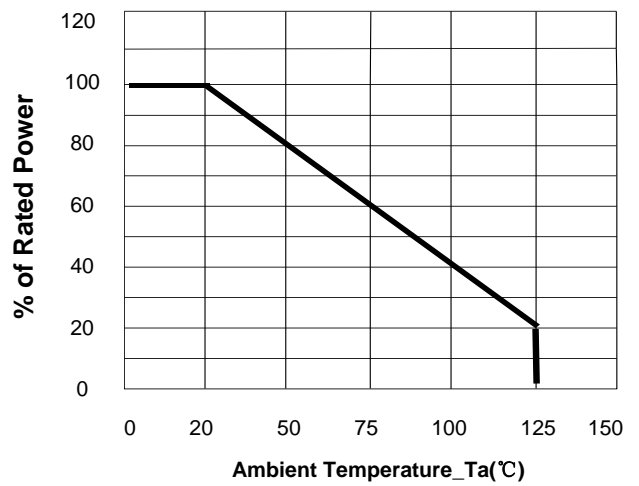
Junction Capacitance vs. Reverse Voltage



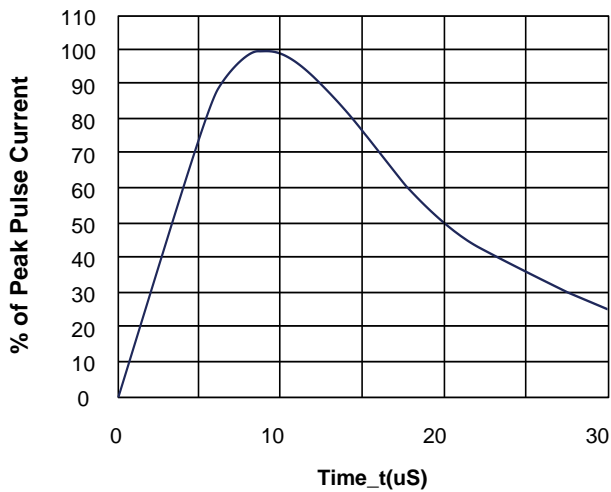
Peak Pulse Power vs. Pulse Time



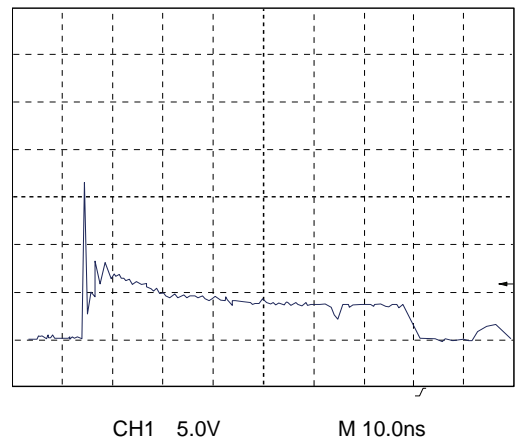
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

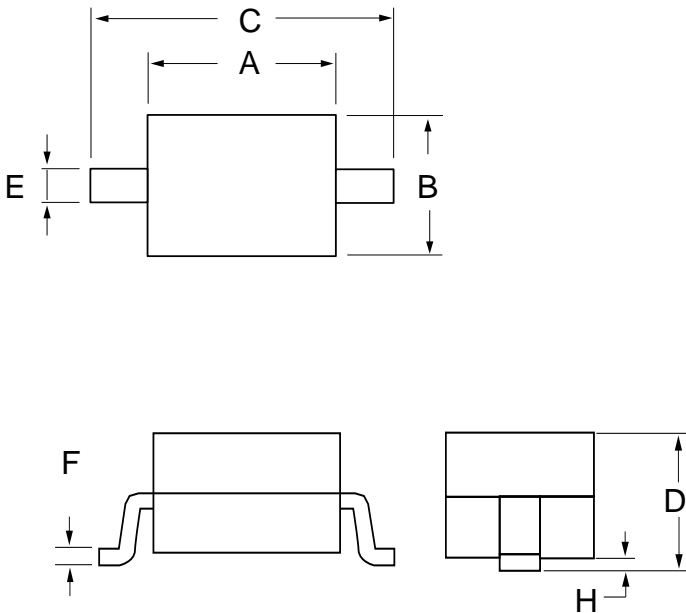


8 X 20uS Pulse Waveform



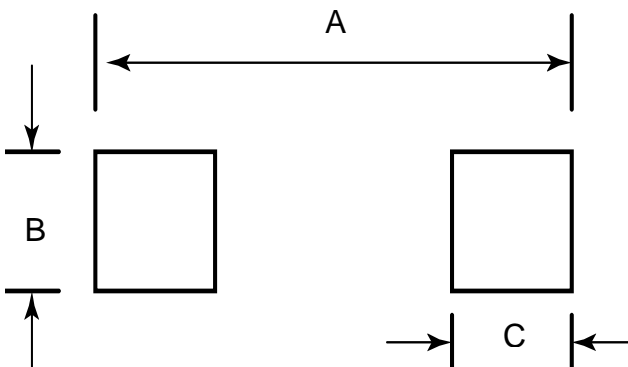
**ESD Clamping Voltage
8 kV Contact per IEC61000-4-2**

SOD-323 Package Outline Drawing



SYM	DIMENSIONS				
	MILLIMETERS			INCHES	
	MIN	NOM	MAX	MIN	MAX
A	1.50	1.65	1.80	0.060	0.071
B	1.20	1.30	1.40	0.045	0.054
C	2.30	2.50	2.70	0.090	0.107
D	-		1.10	-	0.043
E	0.30		0.40	0.012	0.016
F	0.10		0.25	0.004	0.010
H	-		0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

单击下面可查看定价，库存，交付和生命周期等信息

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